

MOS FIELD EFFECT TRANSISTOR

2SJ448

SWITCHING

P-CHANNEL POWER MOS FET

DESCRIPTION

The 2SJ448 is P-channel MOS Field Effect Transistor designed for high voltage switching applications.

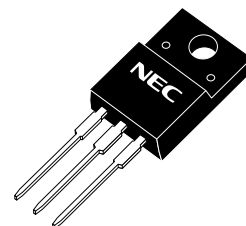
ORDERING INFORMATION

PART NUMBER	PACKAGE
2SJ448	Isolated TO-220

FEATURES

- 250 V rating high withstand voltage
- Low on-state resistance:
 $R_{DS(on)} = 2.0 \Omega \text{ MAX. (} V_{GS} = -10 \text{ V, } I_D = -2.0 \text{ A)}$
- Low input capacitance:
 $C_{iss} = 470 \text{ pF TYP.}$
- Narrow gate cut-off voltage width:
 $V_{GS(off)} = -5.5 \text{ to } -4.0 \text{ V}$
- Built-in gate protection diode
- Full-mold package for easy mounting

★ (Isolated TO-220)



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

Drain to Source Voltage (V _{GS} = 0 V)	V _{DSS}	-250	V
★ Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	± 30	V
Drain Current (DC) (T _C = 25°C)	I _{D(DC)}	± 4.0	A
Drain Current (pulse) ^{Note1}	I _{D(pulse)}	± 16	A
Total Power Dissipation (T _C = 25°C)	P _{T1}	30	W
Total Power Dissipation (T _A = 25°C)	P _{T2}	2.0	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C
Single Avalanche Current ^{Note2}	I _{AS}	-4.0	A
Single Avalanche Energy ^{Note2}	E _{AS}	80	mJ

Notes 1. PW ≤ 10 μs, Duty cycle ≤ 1%

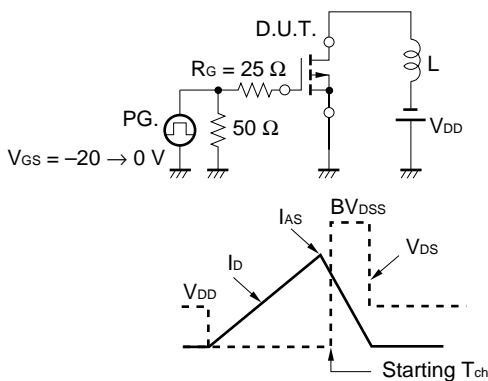
2. Starting T_{ch} = 25°C, V_{DD} = -125 V, R_G = 25 Ω, V_{GS} = -20 → 0 V

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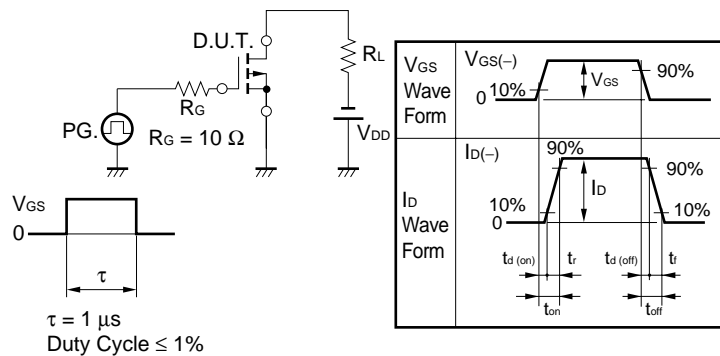
ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Characteristics	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -250 V, V _{GS} = 0 V			-100	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ± 25 V, V _{DS} = 0 V			± 10	μA
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = -10 V, I _D = -1 mA	-4.0	-4.8	-5.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} = -10 V, I _D = -2.0 A	1.0	2.3		S
Drain to Source On-state Resistance	R _{DS(on)}	V _{GS} = -10 V, I _D = -2.0 A		1.5	2.0	Ω
Input Capacitance	C _{iss}	V _{DS} = -10 V		470		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V		200		pF
Reverse Transfer Capacitance	C _{rss}	f = 1 MHz		70		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = -125 V, I _D = -2.0 A		13		ns
Rise Time	t _r	V _{GS} = -10 V		7		ns
Turn-off Delay Time	t _{d(off)}	R _G = 10 Ω		34		ns
Fall Time	t _f			10		ns
Total Gate Charge	Q _G	V _{DD} = -200 V		15		nC
Gate to Source Charge	Q _{GS}	V _{GS} = -10 V		4		nC
Gate to Drain Charge	Q _{GD}	I _D = -4.0 A		9		nC
Body Diode Forward Voltage	V _{F(S-D)}	I _F = 4.0 A, V _{GS} = 0 V		1.0		V
Reverse Recovery Time	t _{rr}	I _F = 4.0 A, V _{GS} = 0 V		195		ns
Reverse Recovery Charge	Q _{rr}	di/dt = 50 A/μs		760		nC

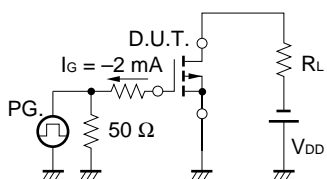
TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME

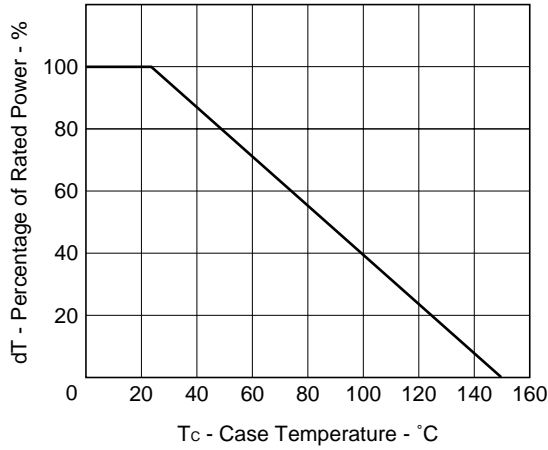


TEST CIRCUIT 3 GATE CHARGE

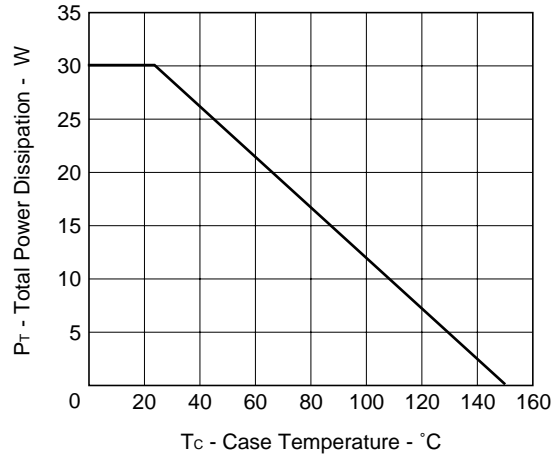


TYPICAL CHARACTERISTICS (T_A = 25°C)

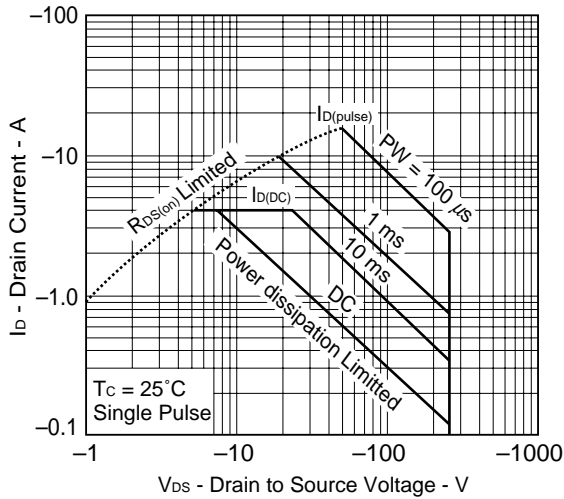
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



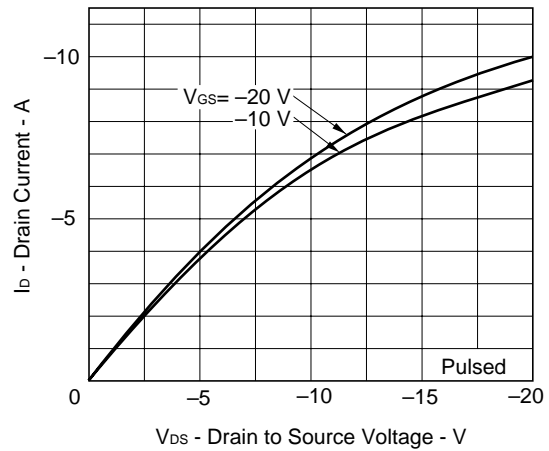
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



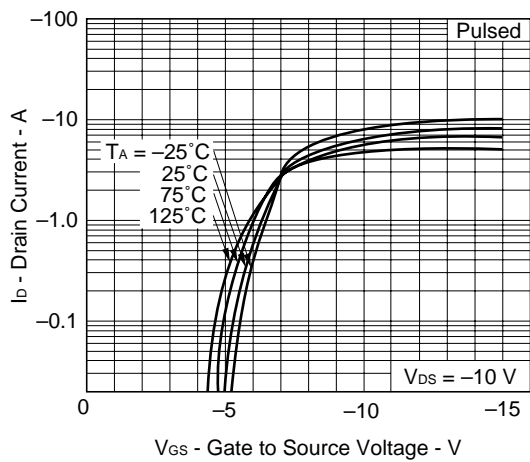
FORWARD BIAS SAFE OPERATING AREA



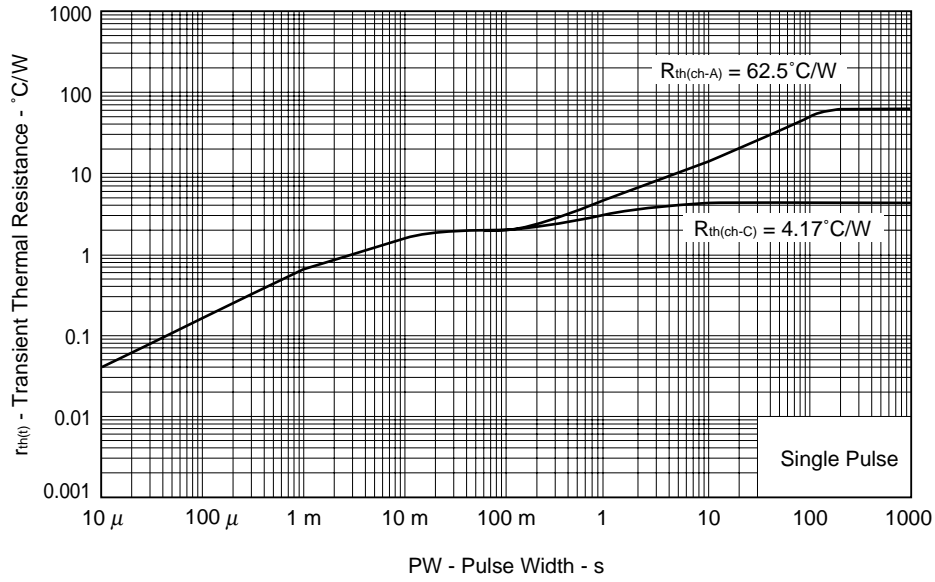
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



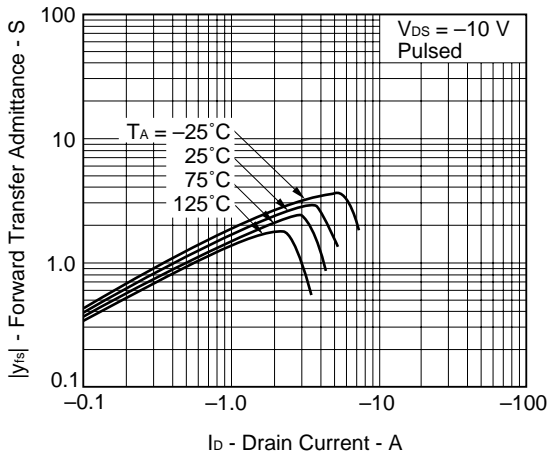
FORWARD TRANSFER CHARACTERISTICS



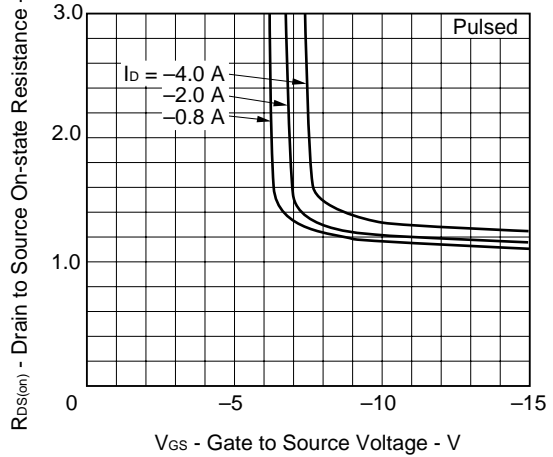
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



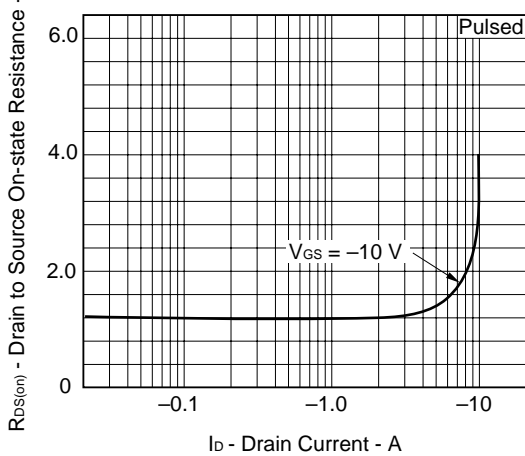
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



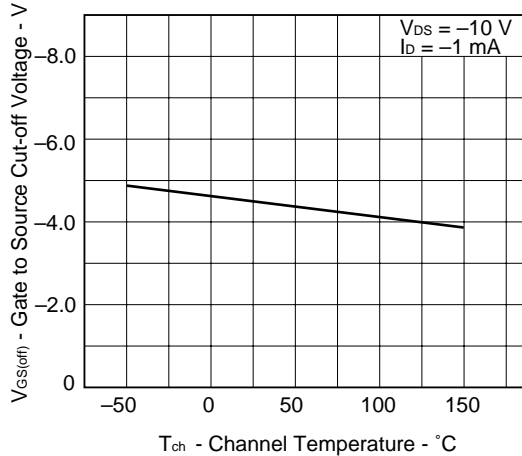
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



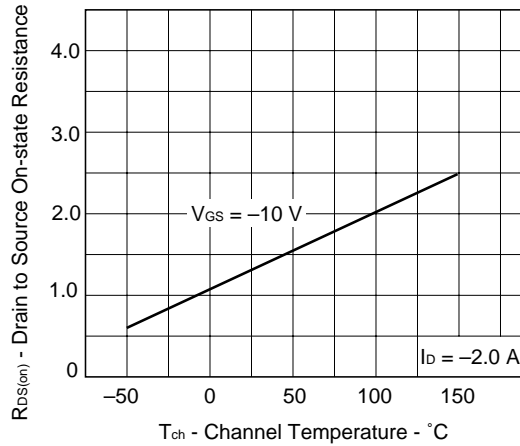
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



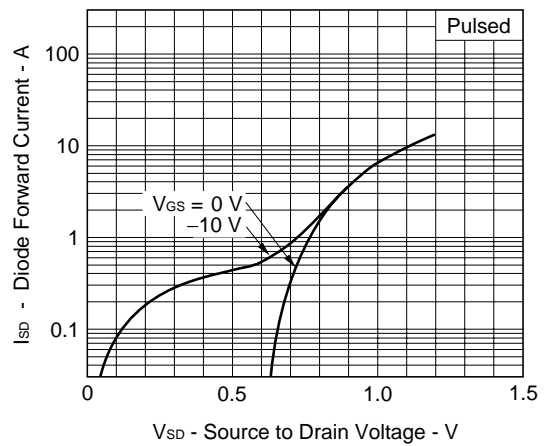
GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



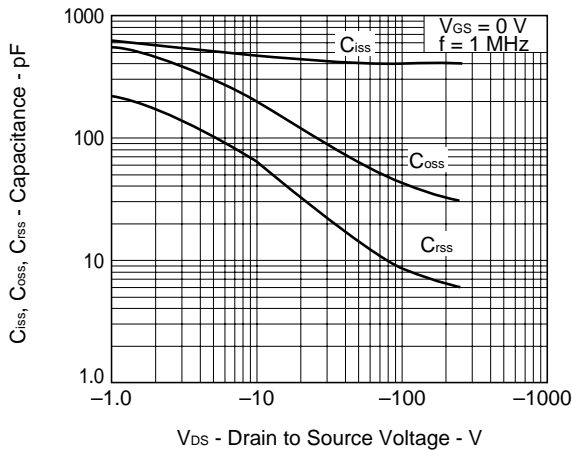
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



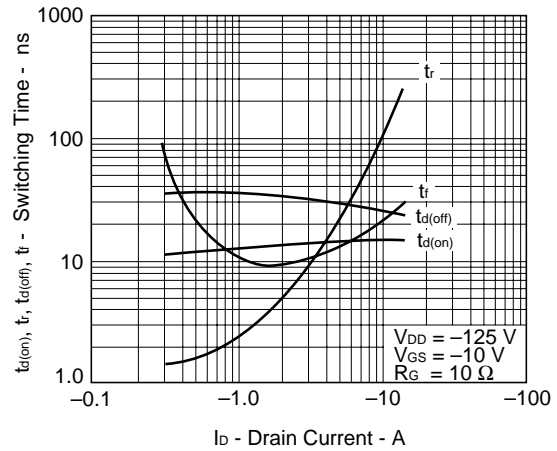
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



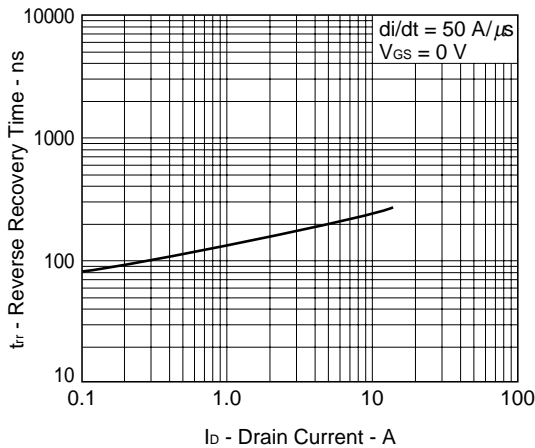
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



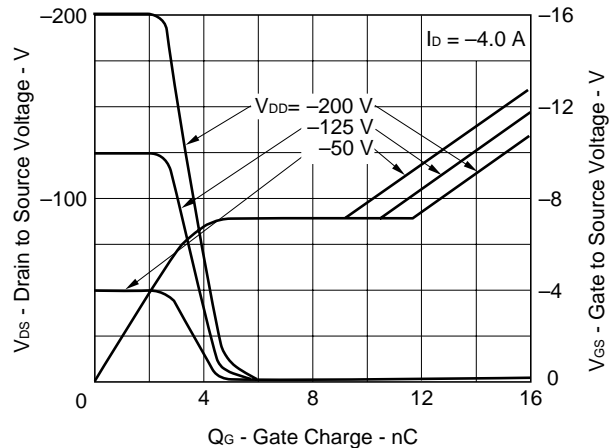
SWITCHING CHARACTERISTICS



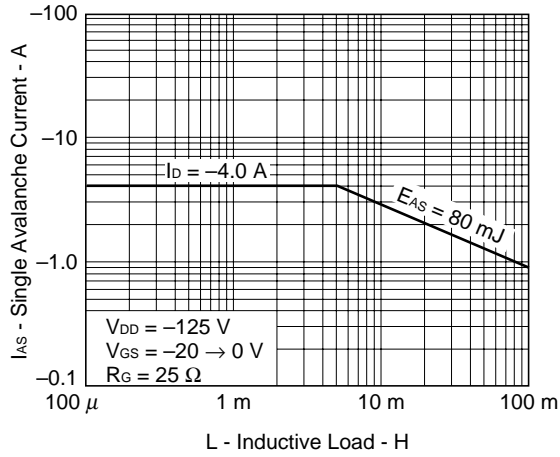
REVERSE RECOVERY TIME vs. DRAIN CURRENT



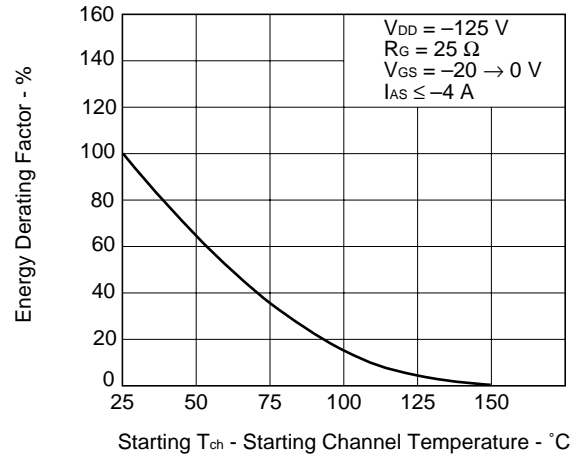
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD

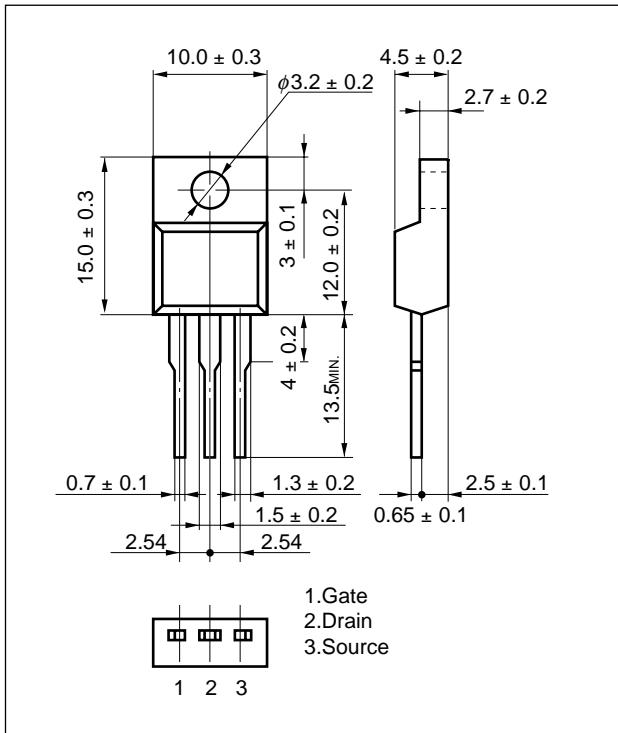


SINGLE AVALANCHE ENERGY DERATING FACTOR

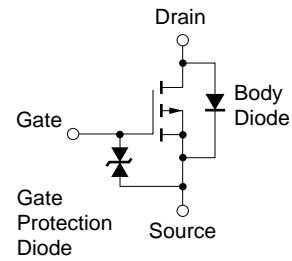


PACKAGE DRAWING (Unit: mm)

Isolated TO-220(MP-45F)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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